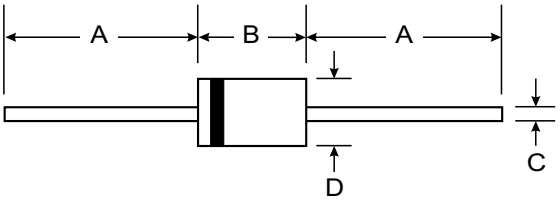
BAW75-BAW76

150mA Axial Leaded High Speed Switching Diodes

Features

- High switching speed: max. 4 ns
- Reverse voltage:max. 25V , 50V
- Peak reverse voltage:max. 35V, 75 V
- Pb / RoHS Free



Mechanical Data

- **Case:** DO-35 Glass Case
- **Weight:** approx. 0.13g

DO-35		
Dim	**Min**	**Max**
A	25.40	—
B	—	4.00
C	—	0.60
D	—	2.00
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics @ T_A = 25°C unless otherwise specified

Parameter		Symbol	Value	Unit
Maximum Peak Reverse Voltage	BAW75 BAW76	V_{RM}	25 50	V
Maximum Reverse Voltage	BAW75 BAW76	V_{RM}	35 75	V
Maximum Average Forward Current Half Wave Recitication with Resistive Load , f ≥ 50Hz		$I_{F(AV)}$	150 (1)	mA
Maximum Power Dissipation		P_D	500 (1)	mW
Maximum Surge Forward Current at t < 1μs , Tj = 25 °C		I_{FSM}	2	A
Maximum Junction Temperature		T_J	200	°C
Storage Temperature Range		T_S	-65 to + 200	°C

Parameter		Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Current	BAW75 BAW76	I_R	V_R = 25 V V_R = 50 V	- -	- -	100 100	nA
Forward Voltage	BAW75 BAW76	V_F	I_F = 30 mA I_F = 100 mA	- -	- -	1.0 1.0	V
Reverse Breakdown Voltage	BAW75 BAW76	$V_{(BR)R}$	Test with 5μA pulses	35 75	- -	- -	V
Diode Capacitance	BAW75 BAW76	Cd	f = 1MHz ; V_R = 0	- -	- -	4.0 2.0	pF
Reverse Recovery Time		Trr	I_F = 10 mA , I_R = 10 mA Irr = 1mA	-	-	4	ns

Note : (1) Valid provided that leads are kept at ambient temperature at a distance of 8mm from case.

FIG. 1 ADMISSIBLE POWER DISSIPATION VERSUS AMBIENT TEMPERATURE

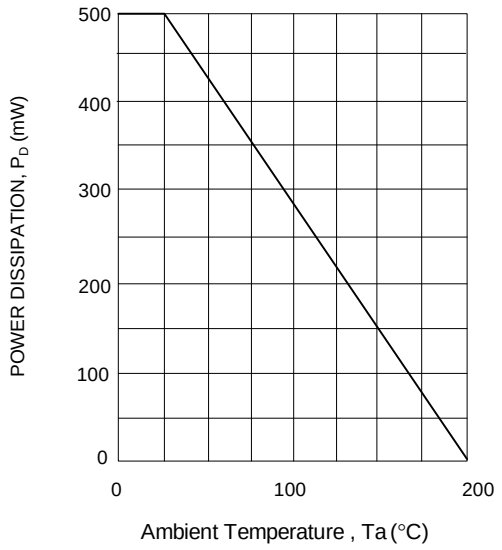


FIG. 2 TYPICAL FORWARD VOLTAGE

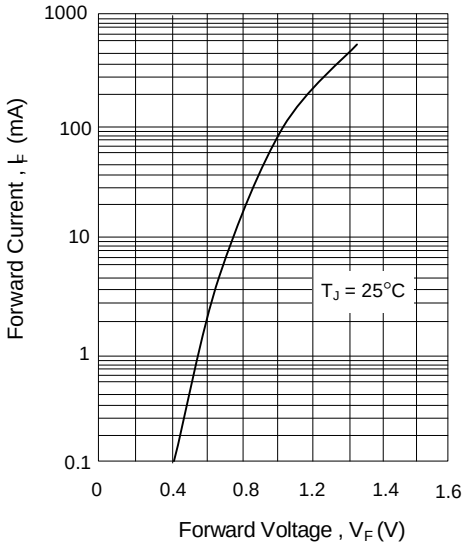


FIG. 3 TYPICAL DIODE CAPACITANCE AS A FUNCTION OF REVERSE VOLTAGE

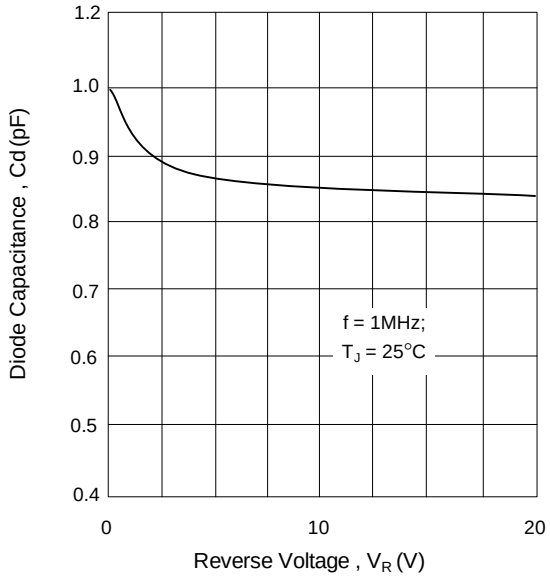


FIG. 4 TYPICAL REVERESE CURRENT VERSUS JUNCTION TEMPERATURE